

**Vishay Siliconix** 

### Precision 8-Ch/Dual 4-Ch Low Voltage Analog Multiplexers

#### DESCRIPTION

The DG3408, DG3409 uses BiCMOS wafer fabrication technology that allows the DG3408/3409 to operate on single and dual supplies. Single supply voltage ranges from 3 V to 12 V while dual supply operation is recommended with  $\pm 3$  V to  $\pm 6$  V.

The DG3408 is an 8-channel single-ended analog multiplexer designed to connect one of eight inputs to a common output as determined by a 3-bit binary address (A<sub>0</sub>, A<sub>1</sub>, A<sub>2</sub>). The DG3409 is a dual 4-channel differential analog multiplexer designed to connect one of four differential inputs to a common dual output as determined by its 2-bit binary address (A0, A1). Break-before-make switching action to protect against momentary crosstalk between adjacent channels.

#### **FEATURES**

- 2.7 V to 12 V single supply or  $\pm$  3 to  $\pm$  6 V dual supply operation
- Low on-resistance  $R_{ON}$ : 3.9  $\Omega$  typ.
- Fast switching: t<sub>ON</sub> - 42 ns, t<sub>OFF</sub> - 24 ns
- Break-before-make guaranteed
- Low leakage
- TTL, CMOS, LV logic (3 V) compatible
- 2000 V ESD protection (HBM)
- MICRO FOOT<sup>®</sup> package
- Lead (Pb)-free solder bumps •
- Compliant to RoHS Directive 2002/95/EC

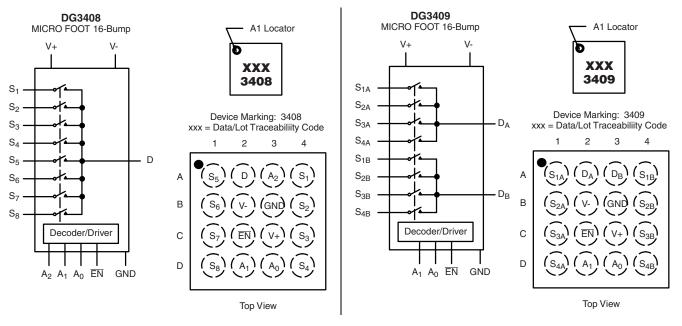
#### **BENEFITS**

- High accuracy
- Single and dual power rail capacity
- Wide operating voltage range
- Simple logic interface

#### **APPLICATIONS**

- Data acquisition systems
- Battery operated equipment
- Portable test equipment
- Sample and hold circuits
- Communication systems
- SDSL, DSLAM
- Audio and video signal routing

#### FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



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COMPLIANT

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TRUTI	TRUTH TABLE (DG3408)								
A <sub>2</sub>	A <sub>1</sub>	A <sub>0</sub>	EN	On Switch					
Х	Х	Х	1	None					
0	0	0	0	1					
0	0	1	0	2					
0	1	0	0	3					
0	1	1	0	4					
1	0	0	0	5					
1	0	1	0	6					
1	1	0	0	7					
1	1	1	0	8					

TRUTH TABLE (DG3409)								
A <sub>1</sub>	A <sub>0</sub> EN On Switch							
Х	Х	1	None					
0	0	0	1					
0	1	0	2					
1	0	0	3					
1	1	0	4					

X = Do not care

For low and high voltage levels for  $V_{AX}$  and  $V_{EN}$  consult "Digital Control" Parameters for Specific V+ operation. See Specifications Tables for:

Single Supply 12 V Dual Supply V+ = 5 V, V- = - 5 V Single Supply 5 V Single Supply 3 V

ORDERING INFORMATION (DG3408)						
Temperature Range	Package	Part Number				
- 40 °C to 85 °C	MICRO FOOT: 16-Bump (4 x 4, 0.5 mm Pitch, 238 μm Bump Height)	DG3408DB-T2-E1 (Lead (Pb)-free)				

ORDERING INFORMATION (DG3409)						
Temperature Range	Package	Part Number				
- 40 °C to 85 °C	MICRO FOOT: 16-Bump (4 x 4, 0.5 mm Pitch, 238 µm Bump Height)	DG3409DB-T2-E1 (Lead (Pb)-free)				

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C, unless otherwise noted)						
Parameter	Limit	Unit				
Voltage Referenced V+ to V-		14				
GND	7	V				
Digital Inputs <sup>a</sup> , V <sub>S</sub> , V <sub>D</sub>		(V-) - 0.3 V to (V) + 0.3 V				
Current (Any Terminal Except S or D)		30				
Continuous Current, S or D)		100	mA			
Peak Current, S or D (Pulsed at 1 ms, 10 % du	ty cycle max).	200				
Package Solder Reflow Conditions <sup>b</sup>	IR/Convection	250	O			
Storage Temperature	- 65 to 150					
Power Dissipation (Package) <sup>c</sup> , ( $T_A = 70 \ ^{\circ}C$ )	16-Bump (4 x 4 mm) MICRO FOOT <sup>d</sup>	719	mW			

Notes:

a. Signals on S<sub>X</sub>, D<sub>X</sub> or IN<sub>X</sub> exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings.

b. Refer to IPC/JEDEC (J-STD-020).

c. All bumps soldered or welded to PC board.

d. Derate 9 mW/°C above 70 °C.

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SPECIFICATIONS (Sing	gle Supply	12 V)						
		Test Conditions Unless Otherwise Specifi V+ = 12 V, ± 10 %, V- = 0			- 4	Limits 0 °C to 85	°C	
Parameter	Symbol	$V_{A}, V_{\overline{EN}} = 0.8 \text{ V or } 2.4 \text{ V}$	rf	Temp. <sup>b</sup>	Min. <sup>c</sup>	Typ. <sup>d</sup>	Max. <sup>c</sup>	Unit
Analog Switch		•						
Analog Signal Range <sup>e</sup>	V <sub>ANALOG</sub>			Full	0		12	V
On-Resistance	R <sub>ON</sub>	V+ = 10.8 V, $V_D$ = 2 V or 9 V, $I_S$ Sequence Each Switch C		Room Full		4	7 7.5	
R <sub>ON</sub> Match Between Channels <sup>g</sup>	$\Delta R_{ON}$			Room			3.6	Ω
On-Resistance Flatness <sup>i</sup>	R <sub>ON</sub> Flatness	V+ = 10.8 V, $V_D$ = 2 V or 9 V, $I_S$ :	= 50 mA	Room			8	
Switch Off Leakage Current	I <sub>S(off)</sub>	V <sub>EN</sub> = 2.4 V, V <sub>D</sub> = 11 V or 1 V, V <sub>S</sub> =	1 V or 11 V	Room Full	- 2 - 20		2 20	
	I <sub>D(off)</sub>	· EN, · D · · · · · · · · · · · · · · · ·		Room Full	- 2 - 20		2 20	nA
Channel On Leakage Current	I <sub>D(on)</sub>	$V_{\overline{EN}} = 0 V, V_{S} = V_{D} = 1 V or$	11 V	Room Full	- 2 - 20		2 20	
Digital Control		•						
Logic High Input Voltage	V <sub>INH</sub>			Full	2.4			v
Logic Low Input Voltage	V <sub>INL</sub>			Full			0.8	•
Input Current	I <sub>IN</sub>	$V_{AX} = V_{\overline{EN}} = 2.4 \text{ V or } 0.8 \text{ V}$		Full	- 1		1	μA
Dynamic Characteristics							r	
Transition Time	t <sub>TRANS</sub>	$V_{S1} = 8 V, V_{S8} = 0 V, (DG34)$ $V_{S1b} = 8 V, V_{S4b} = 0 V, (DG33)$ see figure 2		Room Full		42	71 75	
Break-Before-Make Time	t <sub>BBM</sub>	V <sub>S(all)</sub> = V <sub>DA</sub> = 5 V see figure 4		Room Full	2	24		ns
Enable Turn-On Time	t <sub>ON(EN)</sub>	V <sub>AX</sub> = 0 V, V <sub>S1</sub> = 5 V (DG34 V <sub>AX</sub> = 0 V, V <sub>S1b</sub> = 5 V (DG34		Room Full		42	70 75	
Enable Turn-Off Time	$t_{OFF(\overline{EN})}$	$v_{AX} = 0^{\circ} v, v_{S1b} = 0^{\circ} v$ (DOS) see figure 3	+03)	Room Full		24	44 46	
Charge Injection <sup>e</sup>	Q	$C_L = 1 \text{ nF}, V_{GEN} = 0 \text{ V}, R_{GEN}$	= 0 Ω	Room		29		рС
Off Isolation <sup>e, h</sup>	OIRR	$f = 100 \text{ kHz}, \text{ R}_{\text{L}} = 1 \text{ k}\Omega$		Room		- 80		40
Crosstalk <sup>e</sup>	X <sub>TALK</sub>			Room		- 85		dB
Source Off Capacitance <sup>e</sup>	C <sub>S(off)</sub>	f = 1 MHz, $V_S = 0$ V, $V_{\overline{EN}} = 2.4$ V	DG3408 DG3409	Room Room		21 23		
Drain Off Capacitance <sup>e</sup>	C <sub>D(off)</sub>	$f = 1 \text{ MHz}, V_D = 0 \text{ V}, V_{\overline{\text{EN}}} = 2.4 \text{ V}$	DG3408 DG3409	Room Room		211 112		pF
Drain On Capacitance <sup>e</sup>	C <sub>D(on)</sub>	f = 1 MHz, V <sub>D</sub> = 0 V, V <sub>EN</sub> = 0 V	DG3408 DG3409	Room		238 137		
Power Supplies			200400	Hoom		,	1	
Power Supply Current	l+	$V_{\overline{EN}} = V_A = 0 V \text{ or } V +$		Room			1	μA

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SPECIFICATIONS (Dua	l Supply V	/+ = 5 V, V- = - 5 V)						
		Test Conditions   Unless Otherwise Specifi   V+ = 5 V, V- = - 5 V, ± 10 °			- 4(	Limits ) °C to 85	o°C	
Parameter	Symbol	$V_A$ , $V_{\overline{EN}}$ = 0.8 V or 2 V <sup>f</sup>		Temp. <sup>b</sup>	Min. <sup>c</sup>	Typ. <sup>d</sup>	Max. <sup>c</sup>	Unit
Analog Switch		·			•			
Analog Signal Range <sup>e</sup>	V <sub>ANALOG</sub>			Full	- 5		5	V
On-Resistance	R <sub>ON</sub>	V+ = 4.5 V, V- = - 4.5 V, V <sub>D</sub> = $\pm$ 3.5 V, sequence each switch on	-	Room Full		5	8 8.5	
R <sub>ON</sub> Match Between Channels <sup>g</sup>	$\Delta R_{ON}$			Room			3.6	Ω
On-Resistance Flatness <sup>i</sup>	R <sub>ON</sub> Flatness	V+ = 4.5 V, V- = - 4.5 V, V <sub>D</sub> = ± 3.5 V,	I <sub>S</sub> = 50 mA	Room			8.2	
Switch Off Leakage Current <sup>a</sup>	I <sub>S(off)</sub>	V+ = 5.5, V- = - 5.5 V		Room Full	- 2 - 20		2 20	
Switch On Leakage Current-	I <sub>D(off)</sub>	$V_{\overline{EN}}$ = 2.4 V, $V_{D}$ = ± 4.5 V, $V_{S}$ =	± 4.5 V	Room Full	- 2 - 20		2 20	nA
Channel On Leakage Current <sup>a</sup>	I <sub>D(on)</sub>	V+ = 5.5 V, V- = -5.5 V $V_{\overline{EN}} = 0 V, V_D = \pm 4.5 V, V_S = \pm$	: 4.5 V	Room Full	- 2 - 20		2 20	
Digital Control								
Logic High Input Voltage	V <sub>INH</sub>			Full	2			v
Logic Low Input Voltage	V <sub>INL</sub>						0.8	v
Input Current <sup>a</sup>	I <sub>IN</sub>	V <sub>AX</sub> = V <sub>EN</sub> = 2 V or 0.8 V		Full	- 1		1	μA
Dynamic Characteristics								
Transition Time <sup>e</sup>	t <sub>TRANS</sub>	$V_{S1} = 3.5 \text{ V}, V_{S8} = -3.5 \text{ V}, (DG)$ $V_{S1b} = 3.5 \text{ V}, V_{S4b} = -3.5 \text{ V}, (DG)$ see figure 2		Room Full		68	89 94	
Break-Before-Make Time <sup>e</sup>	t <sub>BBM</sub>	V <sub>S(all)</sub> = V <sub>DA</sub> = 3.5 V see figure 4		Room Full	1	16		ns
Enable Turn-On Time <sup>e</sup>	t <sub>ON(EN)</sub>	V <sub>AX</sub> = 0 V, V <sub>S1</sub> = 3.5 V (DG34 V <sub>AX</sub> = 0 V, V <sub>S1b</sub> = 3.5 V (DG3		Room Full		68	88 94	
Enable Turn-Off Time <sup>e</sup>	$t_{OFF(\overline{EN})}$	$v_{AX} = 0$ V, $v_{S1b} = 3.5$ V (DG3 see figure 3	+03)	Room Full		58	78 81	
Source Off Capacitance <sup>e</sup>	C <sub>S(off)</sub>	f = 1 MHz, V <sub>S</sub> = 0 V, V <sub>EN</sub> = 2 V	DG3408	Room		23		
course on oupdolarioo	3(01)	, , , , , , , , , , , , , , , , , , ,	DG3409	Room		23		
Drain Off Capacitance <sup>e</sup>	C <sub>D(off)</sub>	$f = 1 \text{ MHz}, V_D = 0 \text{ V}, V_{\overline{EN}} = 2 \text{ V}$		Room		223		pF
		DG3409		Room Room		113 246		
Drain On Capacitance <sup>e</sup>	C <sub>D(on)</sub>	$f = 1 \text{ MHz}, V_D = 0 \text{ V}, V_{\overline{EN}} = 0 \text{ V}$ DG3408		Room		246 137		
Power Supplies		1	2 0.0 100		1	,		
	l+			Room			1	
Power Supply Current	I-	$V_{\overline{EN}} = V_A = 0 V \text{ or } V_+$		Room	- 1			μA

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SPECIFICATIONS (Sir	igle Supply	/ 5 V)						
		Test Conditions   Unless Otherwise Specified   V+ = 5 V, ± 10 %, V- = 0 V			- 40	Limits ) °C to 85	°C	
Parameter	Symbol	$V_A$ , $V_{\overline{EN}} = 0.8$ V or 2 V <sup>f</sup>		Temp. <sup>b</sup>	Min. <sup>c</sup>	Typ. <sup>d</sup>	Max. <sup>c</sup>	Unit
Analog Switch	-	L						
Analog Signal Range <sup>e</sup>	V <sub>ANALOG</sub>			Full	0		5	V
On-Resistance	R <sub>ON</sub>	V+ = 4.5 V, V <sub>D</sub> or V <sub>S</sub> = 1 V or 3.5 V,	I <sub>S</sub> = 50 mA	Room Full		7	10.5 11	
R <sub>ON</sub> Match Between Channels <sup>g</sup>	$\Delta R_{ON}$			Room			3.6	Ω
On-Resistance Flatness <sup>i</sup>	R <sub>ON</sub> Flatness	V+ = 4.5 V, V <sub>D</sub> = 1 V or 3.5 V, I <sub>S</sub> =	= 50 mA	Room			9	
Switch Off Leakage Current <sup>a</sup>	I <sub>S(off)</sub>	V+ = 5.5 V		Room Full	- 2 - 20		2 20	
Switch On Leakage Guirent	I <sub>D(off)</sub>	$V_{S} = 1 V \text{ or } 4 V, V_{D} = 4 V \text{ or}$	1 V	Room Full	- 2 - 20		2 20	nA
Channel On Leakage Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{\rm D} = V_{\rm S} = 1 \ V \ {\rm or} \ 4 \ V, \ {\rm sequence} \ {\rm each}$	n switch on	Room Full	- 2 - 20		2 20	
Digital Control		-		_	-			
Logic High Input Voltage	V <sub>INH</sub>	V+ = 5 V		Full	2			v
Logic Low Input Voltage	V <sub>INL</sub>			Full			0.8	v
Input Current <sup>a</sup>	I <sub>IN</sub>	$V_{AX} = V_{\overline{EN}} = 2 V \text{ or } 0.8 V$		Full	- 1		1	μA
Dynamic Characteristics		-			-			
Transition Time <sup>e</sup>	t <sub>TRANS</sub>	$V_{S1} = 3.5 \text{ V}, V_{S8} = 0 \text{ V}, (DG34)$ $V_{S1b} = 3.5 \text{ V}, V_{S4b} = 0 \text{ V}, (DG3)$ see figure 2		Room Full		73	94 104	
Break-Before-Make Time <sup>e</sup>	t <sub>OPEN</sub>	$V_{S(all)} = V_{DA} = 3.5 V$ see figure 4		Room Full	2	29		ns
Enable Turn-On Time <sup>e</sup>	t <sub>ON(EN)</sub>	V <sub>AX</sub> = 0 V, V <sub>S1</sub> = 3.5 V (DG34 V <sub>AX</sub> = 0 V, V <sub>S1b</sub> = 3.5 V (DG34		Room Full		74	94 104	
Enable Turn-Off Time <sup>e</sup>	$t_{OFF(\overline{EN})}$	see figure 3		Room Full		38	57 61	
Charge Injection <sup>e</sup>	Q	$C_L$ = 1 nF, $R_{GEN}$ = 0 $\Omega$ , $V_{GEN}$ =	= 0 V	Room		20		рС
Off Isolation <sup>e, h</sup>	OIRR	- R <sub>L</sub> = 1 kΩ, f = 100 kHz		Room		- 81		dB
Crosstalk <sup>e</sup>	X <sub>TALK</sub>			Room		- 85		
Source Off Capacitance <sup>e</sup>	C <sub>S(off)</sub>	$f = 1 \text{ MHz}, \text{ V}_{S} = 0 \text{ V}, \text{ V}_{\overline{\text{EN}}} = 0 \text{ V}$	DG3408 DG3409	Room Room		22 24		
Drain Off Capacitance <sup>e</sup>	C <sub>D(off)</sub>	$f = 1 \text{ MHz}, V_D = 0 \text{ V}, V_{\overline{EN}} = 2 \text{ V}$ DG3408 DG3409		Room Room		223 113		pF
Drain On Capacitance <sup>e</sup>	C <sub>D(on)</sub>	$f = 1 \text{ MHz}, \text{ V}_{D} = 0 \text{ V}, \text{ V}_{\overline{\text{EN}}} = 0 \text{ V}$	DG3408 DG3409	Room Room		244 143		
Power Supplies			000403	ricom	I	140		
Power Supply Current	l+	V <sub>EN</sub> = V <sub>A</sub> = 0 V or V+		Room			1	μA
		//		I	I	I	I	· · ·

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SPECIFICATIONS (Single Supply 3 V)										
		Test Conditions Unless Otherwise Specifi V+ = 3 V, ± 10 %, V- = 0 V			Limits - 40 °C to 85 °C		5 °C			
Parameter	Symbol	$V_{\pm} = 3 \text{ V}, \pm 10 \text{ %}, V_{\pm} = 0.4 \text{ V} \text{ or } 1.8 \text{ V}^{\text{f}}$	v	Temp. <sup>b</sup>	Min. <sup>c</sup>	Typ. <sup>d</sup>	Max. <sup>c</sup>	Unit		
Analog Switch										
Analog Signal Range <sup>e</sup>	V <sub>ANALOG</sub>			Full	0		3	V		
On-Resistance	R <sub>ON</sub>	V+ = 2.7 V, V <sub>D</sub> = 0.5 or 2.2 V, I <sub>S</sub>	= 5 mA	Room Full		12	25.5 26.5			
R <sub>ON</sub> Match Between Channels <sup>g</sup>	$\Delta R_{ON}$	V+ = ± 2.7 V, V <sub>D</sub> = 0.5 V or 2.2 V,	lo – 5 mA	Room			3.6	Ω		
On-Resistance Flatness <sup>i</sup>	R <sub>ON</sub> Flatness	v i = ± 2.7 v, vD = 0.0 v oi 2.2 v, i	15 - 0 117 1	Room			13			
Switch Off Leakage Current <sup>a</sup>	I <sub>S(off)</sub>	V+ = 3.3 V		Room Full	- 2 - 20		2 20			
Switch On Leakage Guirent	I <sub>D(off)</sub>	$V_{S} = 2 \text{ or } 1 \text{ V}, V_{D} = 1 \text{ or } 2$	V	Room Full	- 2 - 20		2 20	nA		
Channel On Leakage Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{\rm H}$ = 3.3 V $V_{\rm D}$ = $V_{\rm S}$ = 1 or 2 V, sequence each	switch on	Room Full	- 2 - 20		2 20			
Digital Control						•				
Logic High Input Voltage	V <sub>INH</sub>			Full	1.8			v		
Logic Low Input Voltage	V <sub>INL</sub>			Full			0.4	v		
Input Current <sup>a</sup>	I <sub>IN</sub>	$V_{AX} = V_{\overline{EN}} = 1.8 \text{ V or } 0.4 \text{ V}$		Full	- 1		1	μA		
Dynamic Characteristics										
Transition Time	t <sub>TRANS</sub>	$V_{S1} = 1.5 V, V_{S8} = 0 V, (DG3-V_{S1b} = 1.5 V, V_{S4b} = 0 V, (DG3-V_{S1b} = 1.5 V, V_{S4b} = 0 V, (DG3-See figure 2)$	408) 3409)	Room Full		140	165 182			
Break-Before-Make Time	t <sub>BBM</sub>	V <sub>S(all)</sub> = V <sub>DA</sub> = 1.5 V see figure 4		Room Full	2	63		ns		
Enable Turn-On Time	t <sub>ON(EN)</sub>	V <sub>AX</sub> = 0 V, V <sub>S1</sub> = 1.5 V (DG34 V <sub>AX</sub> = 0 V, V <sub>S1b</sub> = 1.5 V (DG3	408)	Room Full		140	162 178			
Enable Turn-Off Time	$t_{OFF(\overline{EN})}$	see figure 3		Room Full		76	97 104			
Charge Injection <sup>e</sup>	Q	$C_L = 1 \text{ nF}, R_{GEN} = 0, V_{GEN} =$	0 V	Room		7		рС		
Off Isolation <sup>e, h</sup>	OIRR	f = 100 kHz, R <sub>I</sub> = 1 kΩ		Room		- 81		dB		
Crosstalk <sup>e</sup>	X <sub>TALK</sub>		T	Room		- 85		uD		
Source Off Capacitance <sup>e</sup>	$C_{S(off)}$	f = 1 MHz, $V_S$ = 0 V, $V_{\overline{EN}}$ = 1.8 V	DG3408 DG3409	Room Room		23 25				
Drain Off Capacitance <sup>e</sup>	C <sub>D(off)</sub>	f = 1 MHz, V <sub>D</sub> = 0 V, V <sub>EN</sub> = 1.8 V	DG3408	Room		230		pF		
Drain On Capacitance <sup>e</sup>	C <sub>D(on)</sub>	f = 1 MHz, V <sub>D</sub> = 0 V, V <sub>EN</sub> = 0 V	DG3409 DG3408	Room Room		120 256				
Diam On Capacitance	CD(on)	$\cdots$	DG3409	Room		147				
Power Supplies						1				
Power Supply Current	l+	$V_{\overline{EN}} = V_A = 0 V \text{ or } V_+$		Room			1	μA		

Notes:

a. Leakage parameters are guaranteed by worst case test condition and not subject to production test.

b. Room = 25 °C, Full = as determined by the operating temperature suffix.

c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.

d. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.

e. Guaranteed by design, not subject to production test.

f. V<sub>IN</sub> = input voltage to perform proper function.

g.  $\Delta R_{DON} = R_{DON} Max - R_{DON} Min$ .

h. Worst case isolation occurs on Channel 4 due to proximity to the drain pin.

i. R<sub>DON</sub> flatness is measured as the difference between the minimum and maximum measured values across a defined Analog signal.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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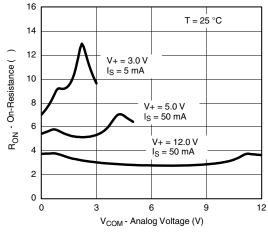
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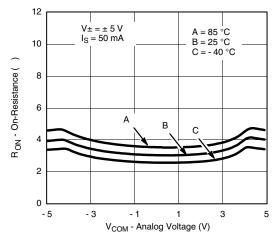


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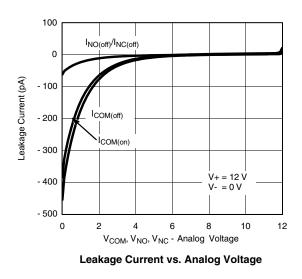
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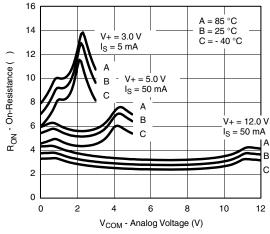


 $\mathbf{R}_{\text{ON}}$  vs.  $\mathbf{V}_{\text{COM}}$  and Single Supply Voltage

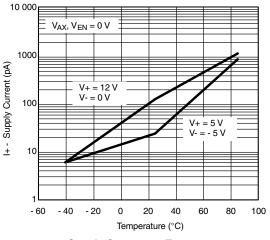


R<sub>ON</sub> vs. Analog Voltage and Temperature

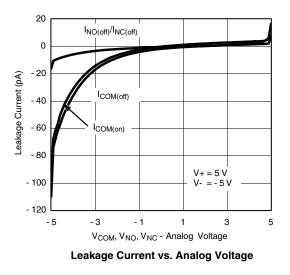




R<sub>ON</sub> vs. Analog Voltage and Temperature



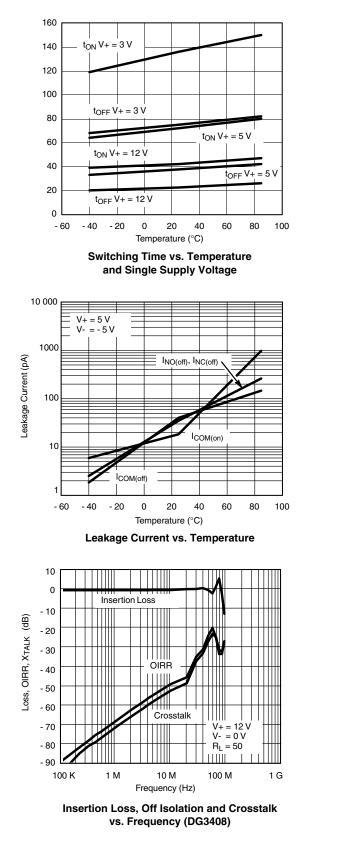
Supply Current vs. Temperature

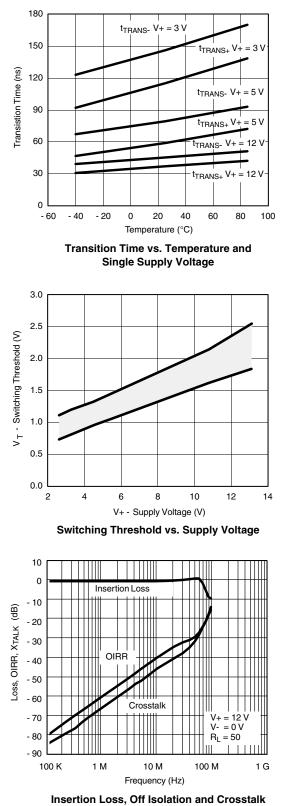


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### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)





vs. Frequency (DG3409)

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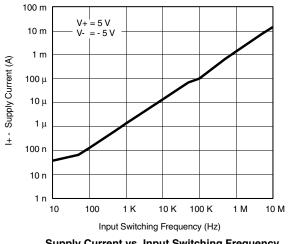
Product is End of Life



### DG3408, DG3409

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#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Supply Current vs. Input Switching Frequency

#### SCHEMATIC DIAGRAM (Typical Channel)

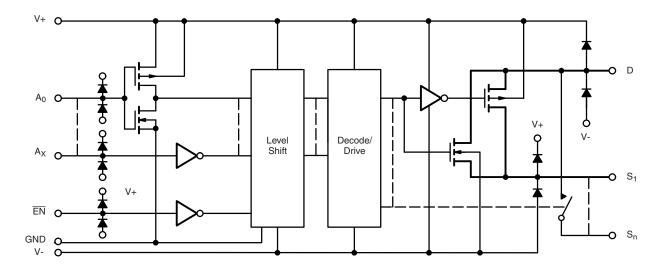
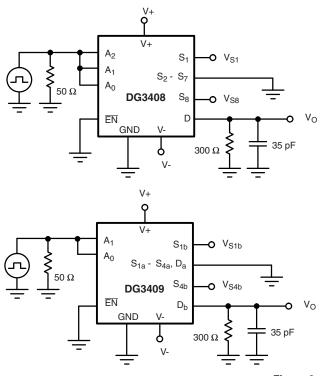
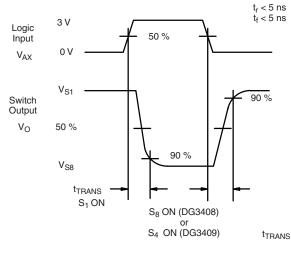


Figure 1.

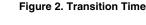
Vishay Siliconix

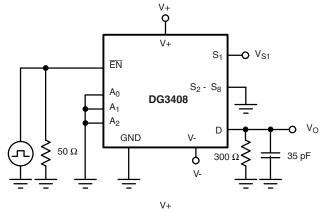
### **TEST CIRCUITS**

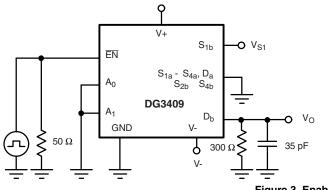


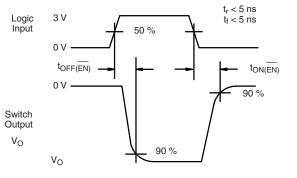


Return to Specifications: Single Supply 12 V Dual Supply V+ = 5 V, V- = - 5 V Single Supply 5 V Single Supply 3 V





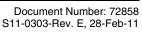




Return to Specifications: Single Supply 12 V Dual Supply V+ = 5 V, V- = - 5 V Single Supply 5 V Single Supply 3 V

Figure 3. Enable Switching Time

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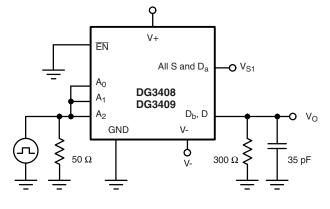
### Product is End of Life

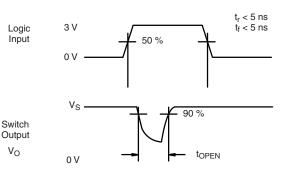


### DG3408, DG3409

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**TEST CIRCUITS** 



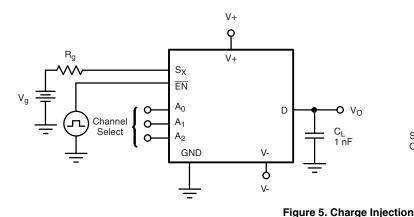


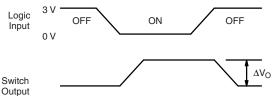
Return to Specifications: Single Supply 12 V Dual Supply V+ = 5 V, V- = - 5 V Single Supply 5 V Single Supply 3 V

#### Figure 4. Break-Before-Make Interval

Switch

Vo





 $\Delta V_O$  is the measured voltage due to charge transfer error Q, when the channel turns off.

 $Q = C_L \times \Delta V_O$ 

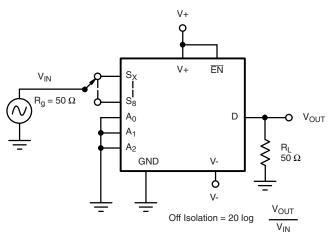


Figure 6. Off Isolation

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### **TEST CIRCUITS**

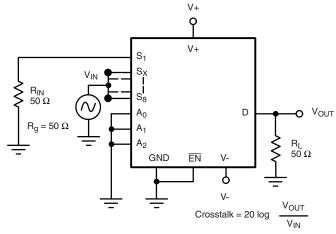
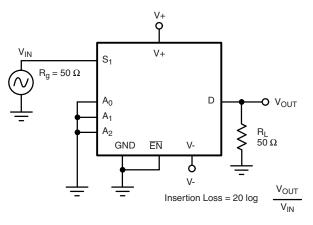
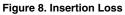


Figure 7. Crosstalk





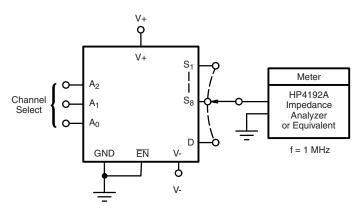


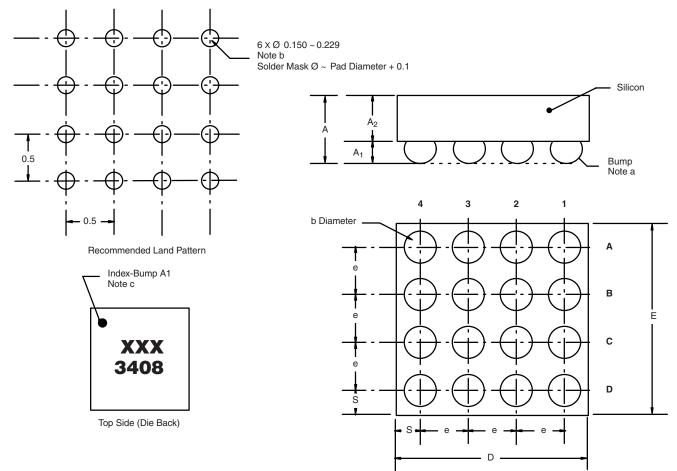
Figure 9. Source Drain Capacitance



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#### **PACKAGE OUTLINE**

#### MICRO FOOT: 16-BUMP (4 x 4, 0.5 mm PITCH, 0.238 mm BUMP HEIGHT)



Notes (Unless Otherwise Specified):

a. Bump is Lead Free Sn/Ag/Cu.

b. Non-solder mask defined copper landing pad.

c. Laser Mark on silicon die back; back-lapped, no coating. Shown is not actual marking; sample only.

	Millim	neters <sup>a</sup>	ches	
Dim.	Min.	Max.	Min.	Max.
Α	0.688	0.753	0.0271	0.0296
A <sub>1</sub>	0.218	0.258	0.0086	0.0102
A <sub>2</sub>	0.470	0.495	0.0185	0.0195
b	0.306	0.346	0.0120	0.0136
D	1.980	2.020	0.0780	0.0795
E	1.980	2.020	0.0780	0.0795
е	0.5 E	BASIC	0.0197 BASIC	
S	0.230	0.270	0.0091	0.0106

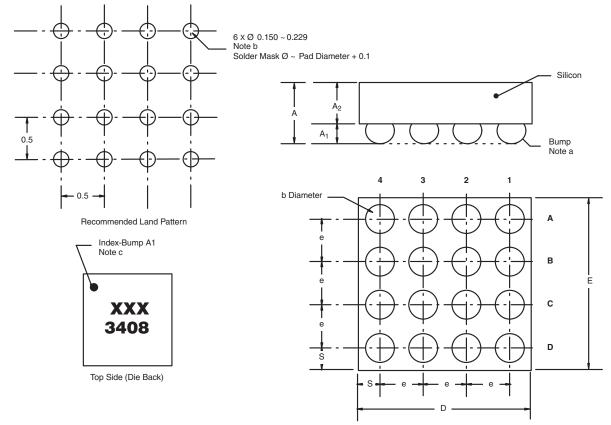
Notes:

a. Use millimeters as the primary measurement.

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### MICRO FOOT: 16-BUMP (4 mm x 4 mm, 0.5 mm PITCH, 0.238 mm BUMP HEIGHT)

#### Notes

(unless otherwise specified)

a. Bump is lead (Pb)-free Sn/Ag/Cu.

b. Non-solder mask defined copper landing pad.

c. Laser mark on silicon die back; back-lapped, no coating. Shown is not actual marking; sample only.

DIM.	MILLIM	ETERS <sup>a</sup>	INC	HES	
DIM.	MIN.	MAX.	MIN.	MAX.	
А	0.688	0.753	0.0271	0.0296	
A <sub>1</sub>	0.218	0.258	0.0086	0.0102	
A <sub>2</sub>	0.470	0.495	0.0185	0.0195	
b	0.306	0.346	0.0120	0.0136	
D	1.980	2.020	0.0780	0.0795	
E	1.980	2.020	0.0780	0.0795	
е	0.5 E	BASIC	0.0197 BASIC		
S	0.230	0.270	0.0091	0.0106	

#### Note

a. Use millimeters as the primary measurement.

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Document Number: 63273 Revision: 13-Jun-11

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